

Trench MOS Barrier Schottky Rectifier

TSP3L100A

SMA



Cathode  Anode

Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (TJ = 25°C unless otherwise noted)

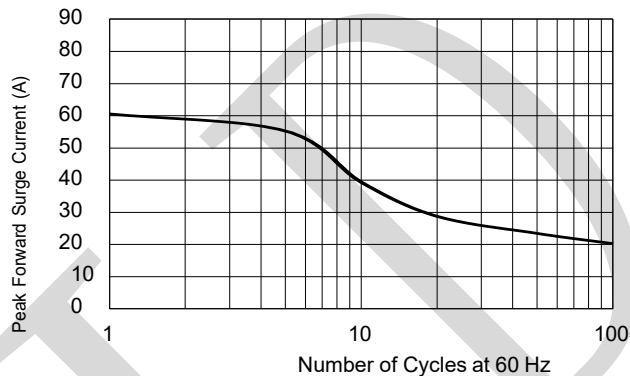
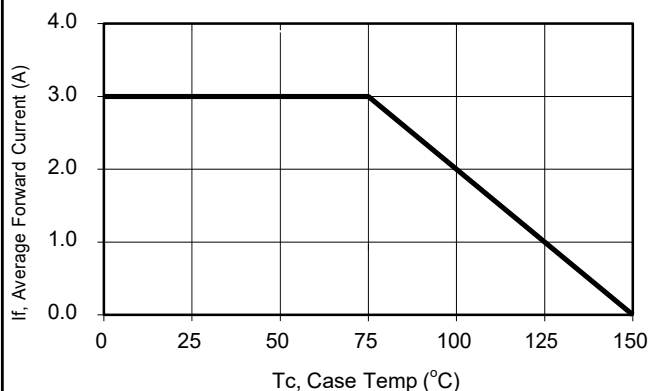
Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			VRRM	100		V
Maximum average forward rectified current			IF(AV)	3		A
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode			IFSM	60		A
Operating junction and storage temperature range			TJ, TSTG	-50 to +150		°C
Typical thermal resistance per diode (Mounted on FR-4 PCB)			RθJA	150		°C/W
Instantaneous forward voltage			VF(1)	TYP.	MAX.	V
	IF=3A	TJ=25°C		0.55	0.62	
	IF=3A	TJ=25°C		0.49	-	
Instantaneous reverse current per diode at rated reverse voltage		TJ=25°C	IR(2)	10	50	uA
		TJ=125°C		5	-	mA

Notes:

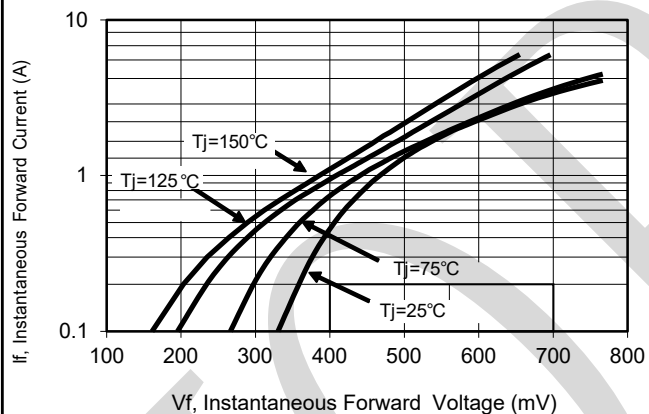
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

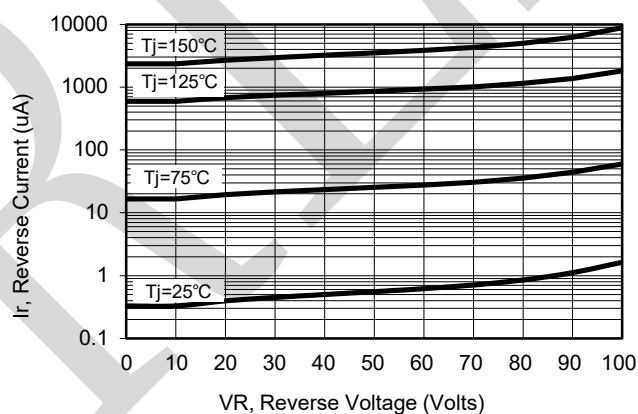
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



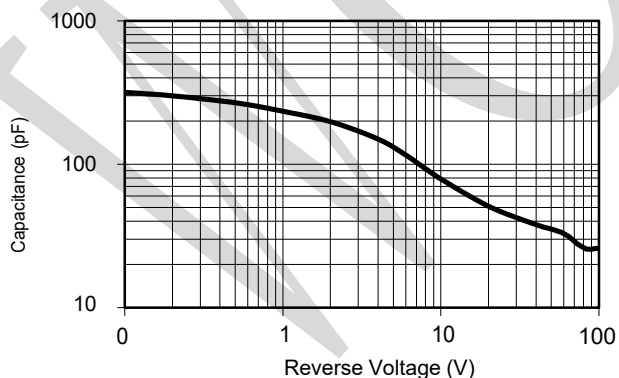
Current Derating, Case



Maximum Repetitive Surge Current



Typical Forward Voltage

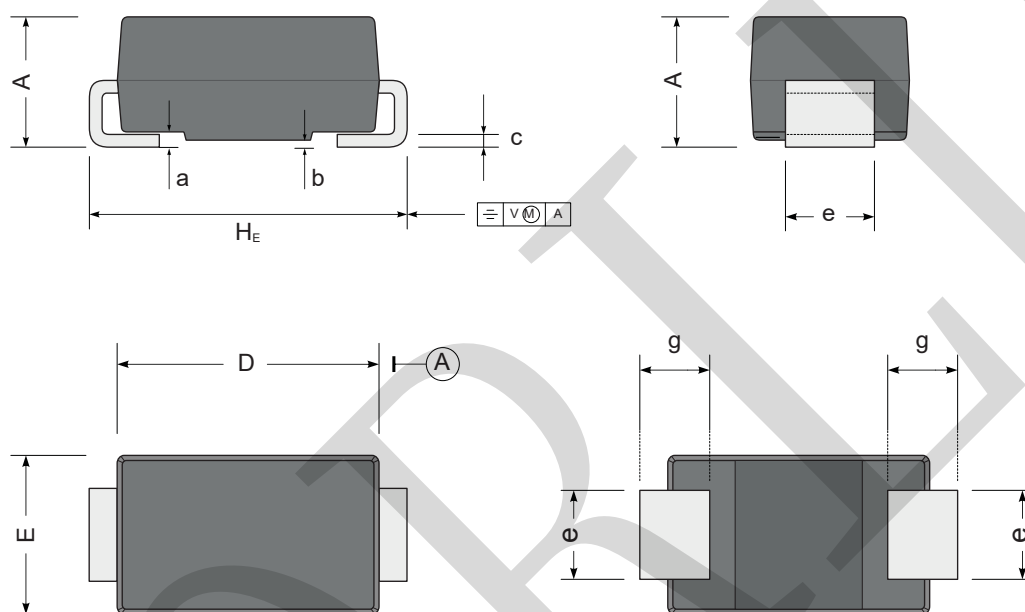


Typical Reverse Current

Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

SMA



UNIT		A	D	E	H _E	c	e	g	b	a
mm	max	2.2	4.5	2.7	5.2	0.31	1.6	1.5	0.2	0.3
	min	1.9	4.0	2.3	4.7	0.15	1.3	0.9	0.05	
mil	max	87	181	106	205	12	63	59	7.9	12
	min	75	157	91	185	6	51	35	2	